BUK9Y21-40E

N-channel 40 V, 21 mΩ logic level MOSFET in LFPAK56 7 May 2013 Product data sheet

1. General description

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} rating of greater than 0.5 V at 175 °C

3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- · Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	33	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	45	W
Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	18.1	21	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 10 \text{ A}; V_{DS} = 32 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$		-	2.7	-	nC



N-channel 40 V, 21 mΩ logic level MOSFET in LFPAK56

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D I
2	S	source		
3	S	source	[qj	G—UHA
4	G	gate	<u>o o o o</u>	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK9Y21-40E	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9Y21-40E	92140E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	40	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω		-	40	V
V_{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-10	10	V
		T _j ≤ 175 °C; Pulsed	[1][2]	-15	15	V
I _D	drain current	$T_{mb} = 25 ^{\circ}C; V_{GS} = 5 V; Fig. 1$		-	33	Α
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 1</u>		-	23	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 4		-	131	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	45	W

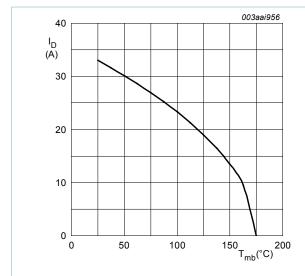
BUK9Y21-40E

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Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
Source-drain	n diode		'			
I _S	source current	T _{mb} = 25 °C		-	33	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	131	Α
Avalanche r	uggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 33 A; $V_{sup} \le 40$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 3	[3][4]	-	12	mJ

- Accumulated pulse duration up to 50 hours delivers zero defect ppm Significantly longer life times are achieved by lowering $\rm T_j$ and or $\rm V_{GS}$
- [2]
- Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [3]
- Refer to application note AN10273 for further information.



Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 5V$$

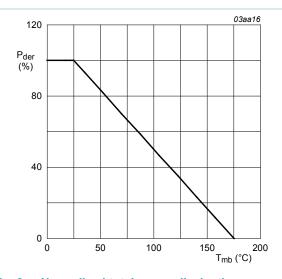


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

N-channel 40 V, 21 m Ω logic level MOSFET in LFPAK56

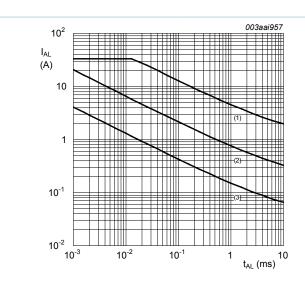
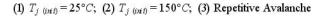


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time



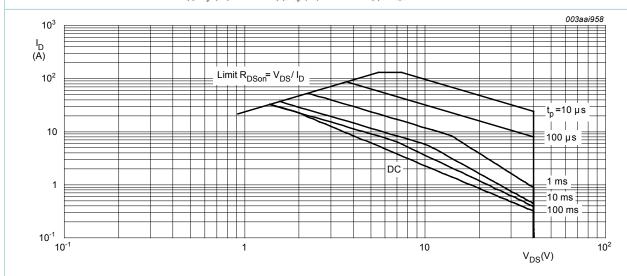


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

9. Thermal characteristics

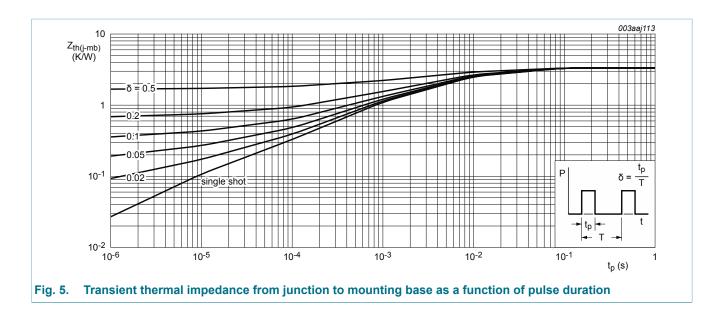
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	3.33	K/W

BUK9Y21-40E

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N-channel 40 V, 21 m Ω logic level MOSFET in LFPAK56



10. Characteristics

Table 7. **Characteristics**

BUK9Y21-40E

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		-			
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	2.45	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	0.5	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-	0.02	1	μA
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	$V_{GS} = 5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 11$	-	18.1	21	mΩ
	resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 11	-	14.4	17	mΩ
		V _{GS} = 5 V; I _D = 10 A; T _j = 175 °C; Fig. 12; Fig. 11	-	-	42.2	mΩ
Dynamic ch	naracteristics		1			
Q _{G(tot)}	total gate charge	I _D = 10 A; V _{DS} = 32 V; V _{GS} = 5 V;	-	7	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	1.2	-	nC

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N-channel 40 V, 21 m Ω logic level MOSFET in LFPAK56

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q_{GD}	gate-drain charge			-	2.7	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;		-	618	824	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	105	127	pF
C _{rss}	reverse transfer capacitance			-	64	88	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R_{L} = 3 Ω ; V_{GS} = 5 V; $R_{G(ext)}$ = 5 Ω ; T_{j} = 25 °C		-	6.2	-	ns
t _r	rise time			-	9.7	-	ns
$t_{d(off)}$	turn-off delay time			-	10.5	-	ns
t _f	fall time			-	8.2	-	ns
Source-drai	in diode						
V_{SD}	source-drain voltage	$I_S = 10 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 ^{\circ}\text{C}$; Fig. 16		-	0.86	1.2	V
t _{rr}	reverse recovery time	I_S = 10 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 25 V; T_j = 25 °C		-	15	-	ns
Q _r	recovered charge			-	7	-	nC

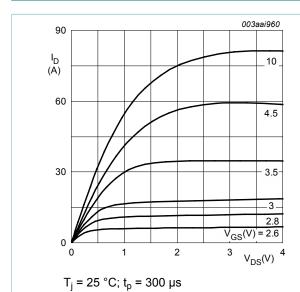


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

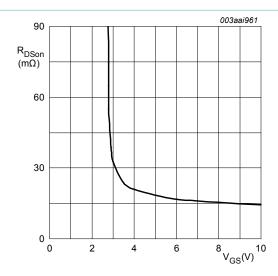


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 10A$$

N-channel 40 V, 21 m Ω logic level MOSFET in LFPAK56

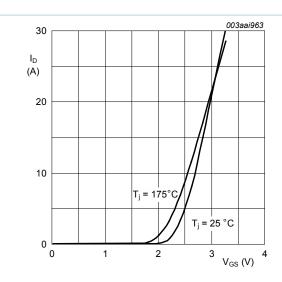


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



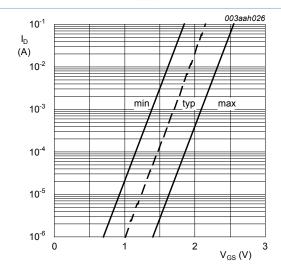


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$

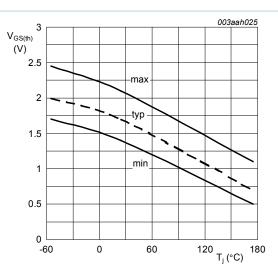
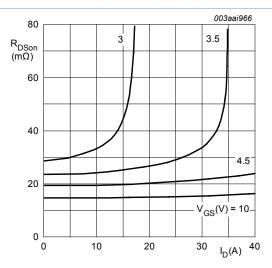


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$



 $T_i = 25 \,^{\circ}\text{C}; t_p = 300 \,\mu\text{s}$

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

N-channel 40 V, 21 mΩ logic level MOSFET in LFPAK56

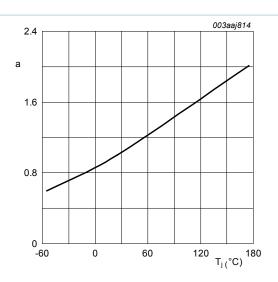


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

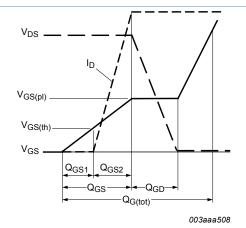


Fig. 14. Gate charge waveform definitions

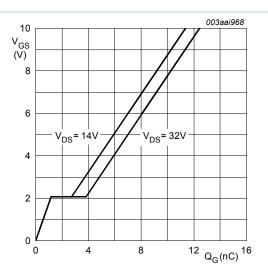


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25$$
°C; $I_D = 10$ A

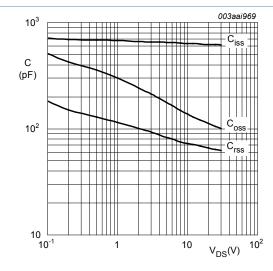


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; \ f = \mathbf{1}MHz$$

N-channel 40 V, 21 m Ω logic level MOSFET in LFPAK56

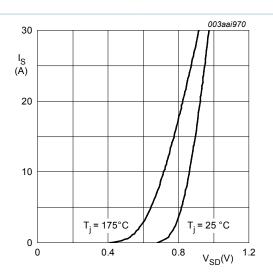


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

11. Package outline

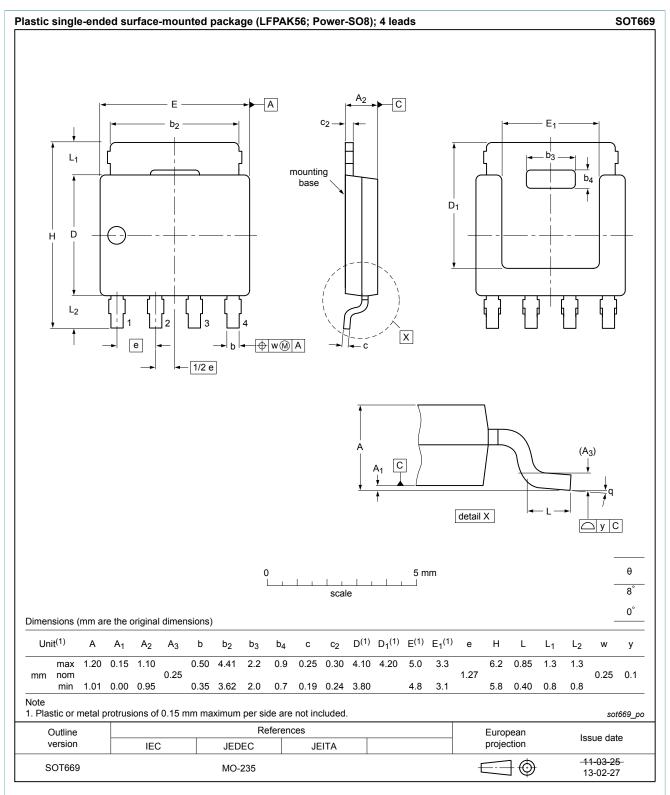


Fig. 17. Package outline LFPAK56; Power-SO8 (SOT669)

BUK9Y21-40E

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N-channel 40 V, 21 mΩ logic level MOSFET in LFPAK56

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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N-channel 40 V, 21 mΩ logic level MOSFET in LFPAK56

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N-channel 40 V, 21 m Ω logic level MOSFET in LFPAK56

13. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	4
10	Characteristics	5
11	Package outline	10
12	Legal information	11
12.1	Data sheet status	11
12.2	Definitions	11
12.3	Disclaimers	11
12.4	Trademarks	12

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